





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	Package	I _D T _C = +25°C
800V	$2.0\Omega@V_{GS} = 10V$	ITO220AB (Type TH)	7A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: ITO220AB (Type TH)
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

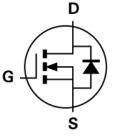




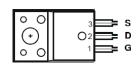




Bottom View



Equivalent Circuit



Top View Pin Out Configuration

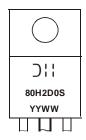
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN80H2D0SCTI	ITO220AB (Type TH)	50 pieces/tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



☐ ☐ Manufacturer's Marking

80H2D0S = Product Type Marking Code

YYWW = Date Code Marking

YY or YY = Last Two Digits of Year (ex: 17 = 2017)

WW or WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	800	V
Gate-Source Voltage			V_{GSS}	±30	V
Continuous Drain Current (Note 9), V _{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	7 4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 9)	I _{DM}	28	Α		
Avalanche Current (Note 6) L = 30mH		I _{AS}	2.0	Α	
Avalanche Energy (Note 6) L = 30mH		Eas	60	mJ	
Peak Diode Recovery dv/dt (Note 7)	dv/dt	2.8	V/ns		

Thermal Characteristics

Characteristic	Symbol	Max	Unit	
Power Dissipation (Note 5) $ T_C = +25^{\circ}C $ $T_C = +100^{\circ}C $		P _D	41 16	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	49.5	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R _{0JC}	3	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

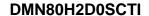
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			,		1			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	800	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	1	_	25	μΑ	$V_{DS} = 800V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	1	_	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	2.0	3.3	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
Static Drain-Source On-Resistance	R _{DS(ON)}	1	1.4	2.0	Ω	$V_{GS} = 10V, I_D = 2.5A$		
Diode Forward Voltage	V_{SD}		0.86	1.5	V	$V_{GS} = 0V, I_S = 7.0A$		
DYNAMIC CHARACTERISTICS (Note 6)								
Input Capacitance	C _{iss}		1253	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		
Output Capacitance	Coss		115	_				
Reverse Transfer Capacitance	C _{rss}	1	11	_				
Gate Resistance	R_g		1.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$		
Total Gate Charge	Q_g	1	35.4	_		$V_{GS} = 10V, V_{DS} = 560V,$ $I_{D} = 7A$		
Gate-Source Charge	Q_{gs}	l	5.9	_	nC			
Gate-Drain Charge	Q_{gd}		16.4	_		ID = /A		
Turn-On Delay Time	t _{D(ON)}	_	20.5	_	ns			
Turn-On Rise Time	t _F	1	35.8	_	ns	$V_{GS} = 10V, V_{DD} = 350V,$		
Turn-Off Delay Time	t _{D(OFF)}	1	104	_	ns	$R_G = 25\Omega$, $I_D = 7A$		
Turn-Off Fall Time	t _F		42.6	_	ns			
Body Diode Reverse Recovery Time	t _{RR}	_	419	_	ns	$dI/dt = 100A/\mu s$, $V_{GS} = 0V$,		
Body Diode Reverse Recovery Charge	Q _{RR}	_	4324		μC	I _F = 7A		

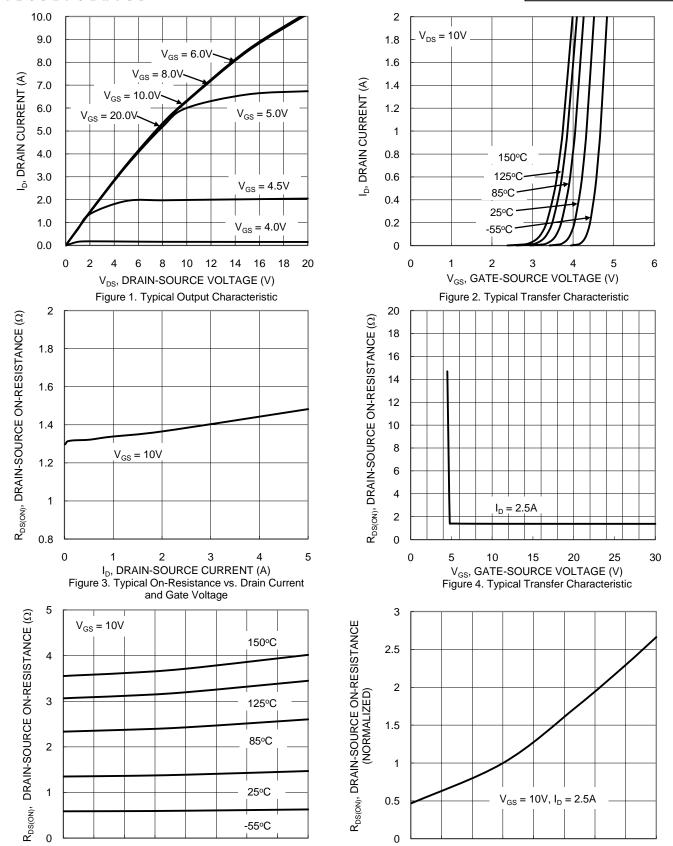
Notes:

- 5. Device mounted on an infinite heatsink.

- Device modified on an illimite heatstirk.
 Guaranteed by design. Not subject to production testing.
 I_{SD} ≤ 4.5A, di/dt ≤ 200A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Drain current limited by maximum junction temperature.







T_J, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Temperature

50

75

100 125

1.5

2

2.5

3

I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current

and Temperature

3.5

0

0

-50

-25

0

25

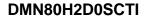
-55°C

4

4.5

5

150





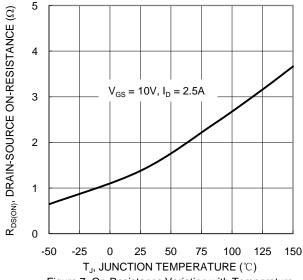
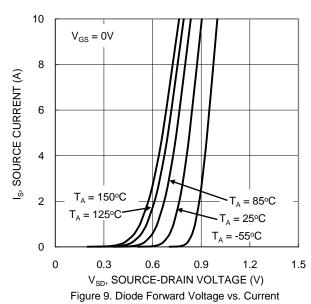


Figure 7. On-Resistance Variation with Temperature



10 8 6 $V_{GS}(V)$ $V_{DS} = 560 V, I_{D} = 7 A$ 4 2 0 0 5 20 25 30 35 40 10 15 Q_q (nC) Figure 11. Gate Charge

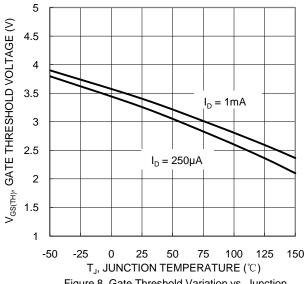
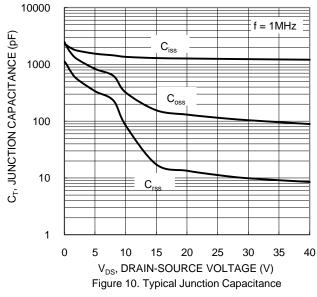
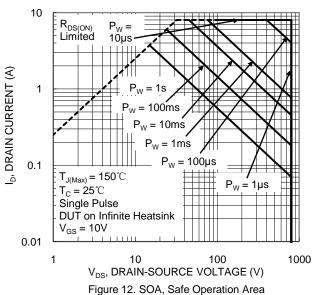


Figure 8. Gate Threshold Variation vs. Junction Temperature







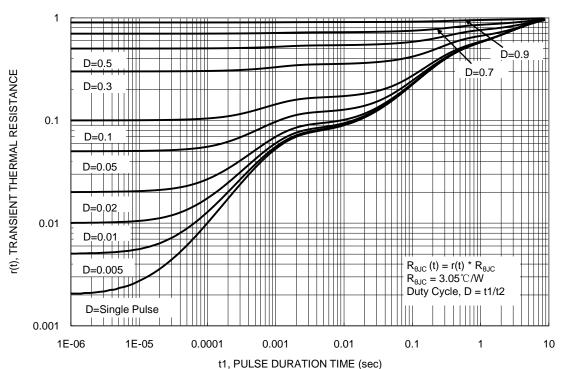


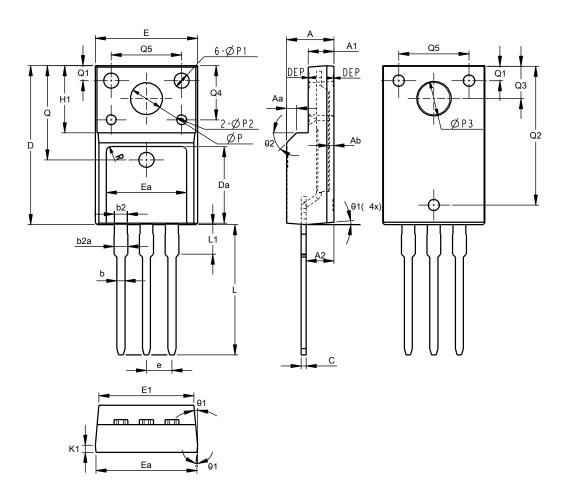
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

ITO220AB (Type TH)



ITO220AB (Type TH)						
Dim	Min	Тур				
Α	4.50	4.90	4.70			
A1	2.34	2.74	2.54			
A2	2.63	2.76				
Aa	2.63 2.89 2.76 1.00 REF					
Ab	0.30	0.60	0.56			
b	0.75	0.90	0.80			
b2	1.23	1.38	1.28			
b2a	1.25	1.45	1.35			
С	0.45	0.60	0.50			
D	15.47	16.27	15.87			
Da	7.55	8.05	7.80			
е	2	.54 BS	С			
Е	9.86	10.46	10.16			
E1	9.26	9.66	9.46			
Ea	7.70	8.30	8.00			
Eb	9.76	10.04				
H1	6.70 REF					
L	12.58	13.38	12.98			
L1	2.81	3.05	2.93			
K 1	0.65	0.75	0.70			
Q	9	.40 RE	F			
Q1	1.00	2.00	1.50			
Q2	13.50	14.30	13.90			
Q3	3.15	3.45	3.30			
Q4	5.15	5.65	5.40			
Q5	6.70	7.30	7.00			
ØΡ	3.06	3.40	3.18			
ØP1	1.40	1.60	1.50			
ØP2	0.95	1.05	1.00			
ØP3	3.30	3.60	3.45			
θ1	3º	7º	5º			
θ2	-	45°	-			
R	0.50 REF					
DEP	0.05 0.15 0.10					
All Dimensions in mm						



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

DMN80H2D0SCTI
Document number: DS39151 Rev. 2 - 2

ПОСТАВКА ЭЛЕКТРОННЫХ КОМПОНЕНТОВ

многоканальный

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001 Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru 4 moschip.ru 9